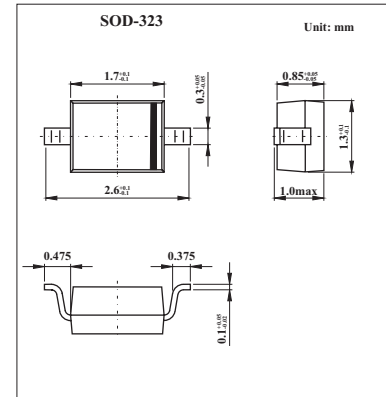


## Silicon Epitaxial Planar Diode

## 1SV269

## ■ Features

- High Capacitance Ratio:  $C_{2V}/C_{25V} = 11.5$  (Typ.)
- Low Series Resistance:  $r_s = 0.55 \Omega$  (Typ.)
- Excellent C-V Characteristics, and Small Tracking Error.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	34	V
Peak Reverse Voltage	$V_{RM}$	36( $R_L = 10 \text{ K } \Omega$ )	V
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	$V_R$	$I_R = 1 \mu\text{A}$	34			V
Reverse Current	$I_R$	$V_R = 32 \text{ V}$			10	nA
Capacitance	$C_{2V}$	$f = 1 \text{ MHz}; V_R = 2 \text{ V}$	33	31.5	34	pF
	$C_{25V}$	$f = 1 \text{ MHz}; V_R = 25 \text{ V}$	2.5	2.75	2.9	
Capacitance Ratio	$C_{2V}/C_{25V}$		11	11.5		
	$C_{25V}/C_{28V}$		1.03	1.05		
Series Resistance	$r_s$	$V_R = 5 \text{ V}, f = 470 \text{ MHz}$		0.55	0.7	$\Omega$

Note :

Available in matched group for capacitance to 2.0%.

$$\frac{C(\text{Max.})-C(\text{Min.})}{C(\text{Min.})} \leq 0.020$$

$(V_R=2\sim 25\text{V})$

## ■ Marking

Marking	TE
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